

*Poster Sessions of the 15<sup>th</sup> International Conference on Narrow Gap Systems*

<b>Poster No</b>	<b>Posters Session 1, Tuesday August 2<sup>nd</sup>, 5-7 PM, Lobby of Hancock Hall Posters Size 110 cm x 85 cm</b>	
<b>1</b>	<b>Effects of Vanadium doping of PbTe</b>	A. A. Dobrovolsky, Moscow State University, Russia
<b>2</b>	<b>Modeling PbTe-based low dimensional structures</b>	M. Bukala, Polish Academy of Sciences, Poland
<b>3</b>	<b>Calculation of thermoelectric coefficients of PbTe using a three-band model of the electron band structure</b>	E. S. Tkacheva, Moscow State University, Russia
<b>4</b>	<b>Novel IV-VI Diluted Magnetic Semiconductors doped with transition metals</b>	E. P. Skipetrov, Moscow State University, Russia
<b>5</b>	<b>Towards Thermoelectric Characterization of Topological Surface States in Exfoliated Bi<sub>2</sub>Te<sub>3</sub> Thin Films</b>	J. Luo, Northwestern University, USA
<b>6</b>	<b>Reduced dimensionality gain in thermoelectric power factor of IV-VI semiconductor nanostructures</b>	E. A. de Andrada e Silva, Inst. Nac. de Pesquisas Espaciais, Brazil
<b>7</b>	<b>Ettingshausen-like Effect in Zero Magnetic Field: Modeling Novel Thermoelectric Effects in Wide-period InAs/GaSb Type II Superlattices</b>	Y. Tang, Northwestern University, USA
<b>8</b>	<b>The role of anti-phase domains in InSb-based structures grown on on-axis and off-axis Ge substrates</b>	M. Debnath, University of Oklahoma, USA
<b>9</b>	<b>Theoretical optimization of Type I GaInNSb/AlGaNSb dilute Antimonide Nitrides quantum well lasers for 3-4microns Mid-IR Wavelengths</b>	A. Kadri, University of Oran, Algeria
<b>10</b>	<b>Optical studies of MnAs/Al(AsSb)/InAs spin LED</b>	A. Stier, SUNY Buffalo, USA
<b>11</b>	<b>Design effects on the material properties of InAs/GaSb superlattices</b>	H. J. Haugan, Air Force Research Laboratory, USA
<b>12</b>	<b>Interband photocurrent in type-II InAs/(GaIn)Sb superlattice</b>	M. H. Degani, Unicamp, Limeira-SP, Brazil
<b>13</b>	<b>Spin-dependent transport in thin film InSb with ferromagnetic CoFe electrodes</b>	Y.-J. Kim, Virginia Tech, USA
<b>14</b>	<b>The THz Beamline and User Lab at Jefferson Lab</b>	J. Michael Klopff, Jefferson Lab, USA
<b>15</b>	<b>The electrical nature of structural defects in InSb synthesized by molecular beam epitaxy on Si (100) and Gas (100)</b>	M. Edirisooriya, Duke University, USA
<b>16</b>	<b>Quantum well infrared photodetectors optimization based on dark current models evaluation</b>	P. P. Favero, Institute for Advanced Studies, S. J. Campos, Brazil

<b>Poster No</b>	<b>Poster Session 2, Thursday August 4th, 5-7 PM, Lobby of Hancock Hall Posters Size 110 cm x 85 cm</b>	
1	<b>Coherent phonon dynamics in short-period InAs/GaSb superlattices</b>	T. Noe, Rice University, USA
2	<b>Electron scattering in InSb quantum wells due to structural defects</b>	T. Mishima, University of Oklahoma, USA
3	<b>Spin Interactions between InAs Two-Dimensional surface electrons and local magnetic moments determined by antilocalization measurements</b>	Yao Zhang, Virginia Tech, USA
4	<b>Spin and phase decoherence in InAs 2DES ring arrays</b>	R. Lillianfeld, Virginia Tech, USA
5	<b>Dependence of the spin coherence length on wire width for quasi-1-dimensional InSb and InAs wires and Bi wire surface states</b>	M. Rudolph, Virginia Tech, USA
6	<b>The InGaAs/InAlAs double quantum wells as starting structures for the quantum logic gates</b>	E. Sheregii, University of Rzeszow, Poland
7	<b>Doped InAs nanowires-first-principles study</b>	M. Galicka, Institute of Physics PAS, Warsaw, Poland
8	<b>Substantial temperature dependence of transverse electron <math>g^*</math>-factor in lead chalcogenide multi-quantum wells</b>	M. Leontiadou, University of Surrey, UK
9	<b>Generation-recombination processes via acoustic phonons in a disordered graphene</b>	V. Mitin, Sunny Buffalo, USA
10	<b>Strain and Confinement Dependence of the Effective Mass of Holes in InSb Quantum Well</b>	C.K. Gaspe, University of Oklahoma, USA
11	<b>The absence of decimal Lande-g factor in narrow-gap semiconductors including heterostructures</b>	M. Saglam, Ankara University, Turkey
12	<b>The Scattering of terahertz radiation from aligned CNT arrays as a function of Carbon nanotube length</b>	S. Ganti, Wright State University, USA
13	<b>MBE growth and optical characterization of AlInSb/GaAs heterostructures</b>	O. S. Komkov, Saint-Petersburg Electrotechnical Univ., Russia
14	<b>Terahertz absorption in MOVPE grown ferromagnetic InMnAs and InMnSb</b>	M. Bhowmick, Virginia Tech, USA
15	<b>Time resolved spectroscopy of MOVPE grown narrow gap III-Mn-V ferromagnetic semiconductors</b>	T. Merritt, Virginia Tech, USA
16	<b>Time resolved differential transmission spectroscopy in InSb-based parabolic multi-quantum wells</b>	M. Bhowmick, Virginia Tech, USA